



DMT10H032SFVW

100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	Rds(on) Max	I⊵ Max Tc = +25°C
100V	$32m\Omega @ V_{GS} = 10V$	35A

Description

This MOSFET is designed to minimize the on-state resistance (RDs(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

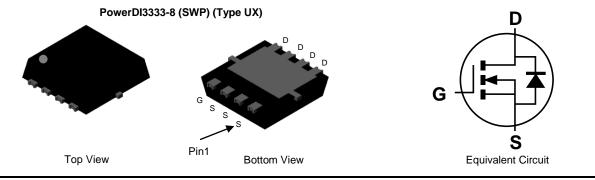
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H032SFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMT10H032SFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

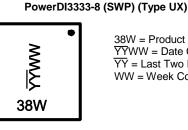
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} 38W = \mbox{Product Type Marking Code} \\ \hline \hline YYWW = \mbox{Date Code Marking} \\ \hline YY = \mbox{Last Two Digits of Year (ex: 20 = 2020)} \\ \hline WW = \mbox{Week Code (01 to 53)} \end{array}$

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Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage		Vgss	±20	V
	Tc = +25°C		35	A
Continuous Drain Current (Note 7) VGS = 10V	T _C = +70°C	ID	28	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	·	Ідм	140	A
Maximum Continuous Body Diode Forward Current (Note 7)	ls	26	A	
Pulsed Body Diode Forward Current (Note 8)	I _{SM}	140	A	
Avalanche Current, L = 0.3mH (Note 8)	las	13	A	
Avalanche Energy, L = 0.3mH (Note 8)		Eas	25.35	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		Po	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	97	°C/W
Total Power Dissipation (Note 6)		PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		R _{θJA}	50	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	2.1	°C/vv	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	100	—		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	VGS(TH)	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	24	32	mΩ	$V_{GS} = 10V, I_D = 7A$	
Diode Forward Voltage	V _{SD}	_	0.86	1	V	$V_{GS} = 0V, I_{S} = 7A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		544	_	pF		
Output Capacitance	Coss		181	_	pF	VDS = 50V, VGS = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	6.0	_	pF		
Gate Resistance	Rg	_	1.2		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg		4.3	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg		8.0	_	nC		
Gate-Source Charge	Qgs	_	1.8		nC	$V_{DS} = 50V, I_D = 7A$	
Gate-Drain Charge	Q _{gd}		2.4	_	nC		
Turn-On Delay Time	tD(ON)		8.5	-	ns		
Turn-On Rise Time	tR	_	2.7	_	ns	VDS = 50V, ID = 7A	
Turn-Off Delay Time	tD(OFF)	_	11.9	_	ns	$V_{GS} = 10V, R_{GEN} = 6\Omega$	
Turn-Off Fall Time	tF	_	6.2		ns		
Reverse Recovery Time	trr		33.2		ns	1- 70 di/dt 1000/up	
Reverse Recovery Charge	Qrr	_	34.3		nC	I _F = 7A, di/dt = 100A/μs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

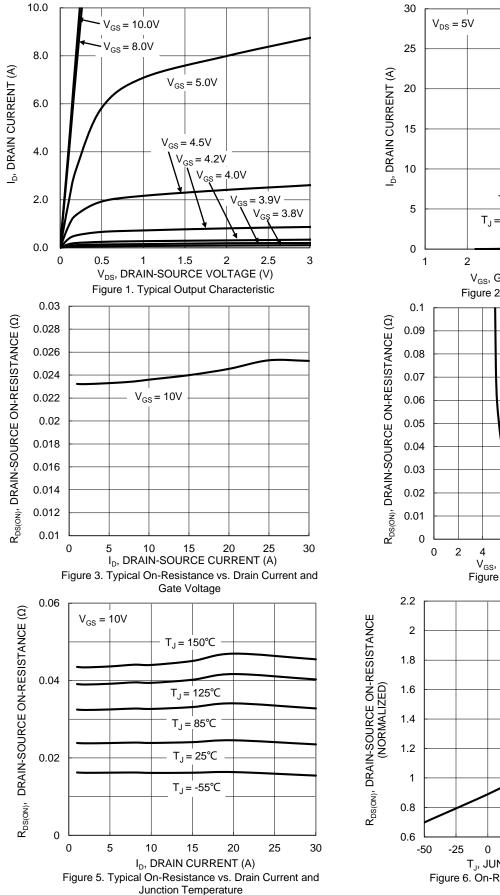
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

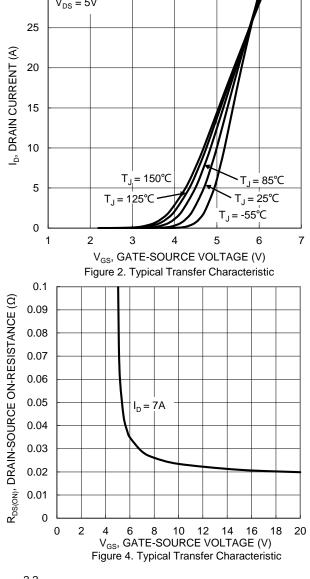
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

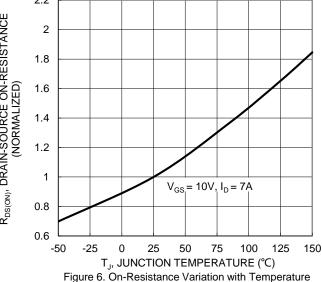
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.



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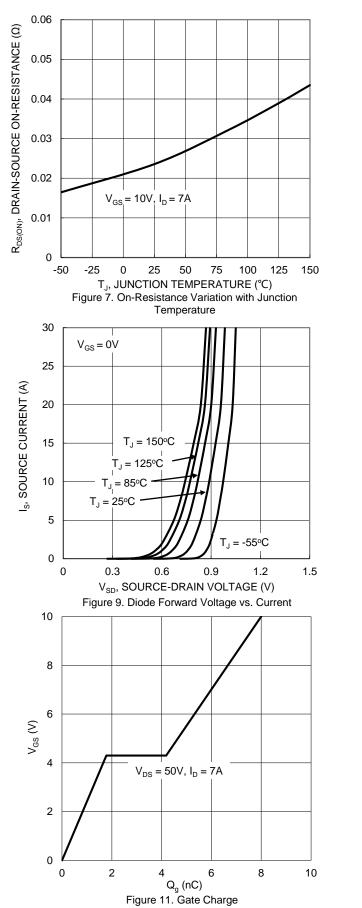


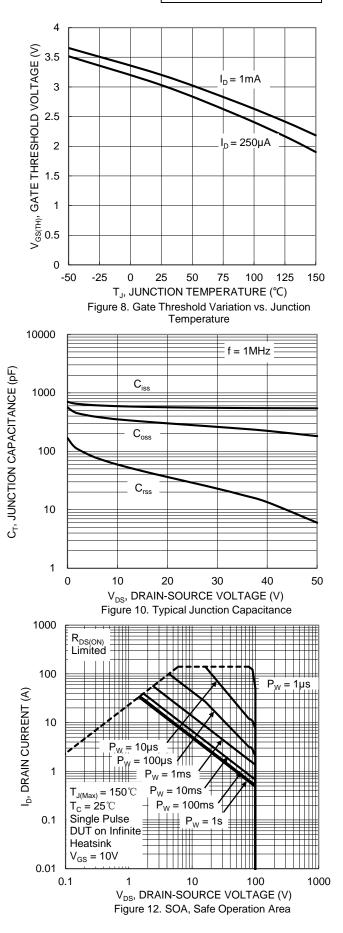




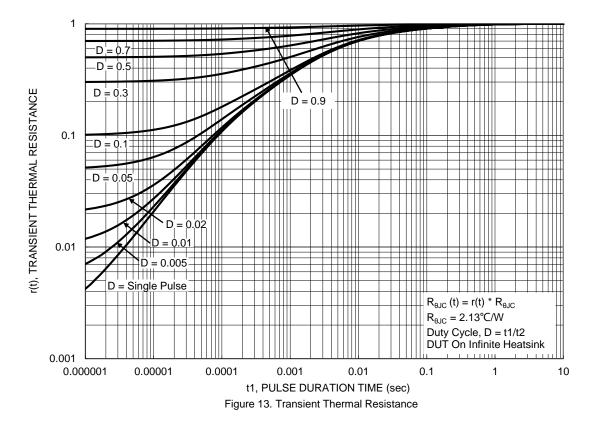


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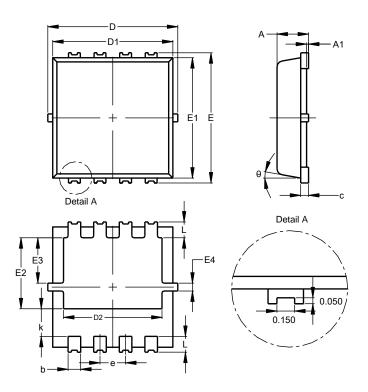






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



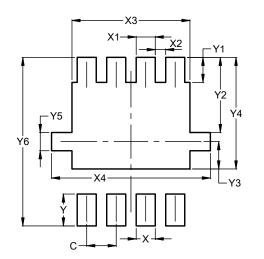
PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min Max Ty				
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е			0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All I	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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